SST5018
P-CHANNEL JFET

Linear Systems replaces discontinued Siliconix SST5018

The SST5018 is a single P-Channel JFET switch

This p-channel analog switch is designed to provide low on-resistance and fast switching.

The SOT-23 package provides ease of manufacturing, and a lower cost assembly option.

(See Packaging Information).

SST5018 Benefits:

- Low Insertion Loss
- No offset or error voltage generated by closed switch
- Purely resistive

SST5018 Applications:

- Analog Switches
- Commutators
- Choppers

FEATURES	
DIRECT REPLACEMENT FOR SILICONIX SST5018	
ZERO OFFSET VOLTAGE	
LOW ON RESISTANCE	$r_{DS(on)} \leq 75\Omega$
ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted)	
Maximum Temperatures	
Storage Temperature	-55°C to +200°C
Operating Junction Temperature	-55°C to +200°C
Maximum Power Dissipation	
Continuous Power Dissipation	500mW
MAXIMUM CURRENT	
Gate Current (Note 1)	I_G = -50mA
MAXIMUM VOLTAGES	
Gate to Drain Voltage	V_{GDS} = 30V
Gate to Source Voltage	V_{GSS} = 30V

SST5018 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
BV_{GSS}	Gate to Source Breakdown Voltage	30	--	--	V	I_G = 1µA, V_{DS} = 0V
$V_{GS(off)}$	Gate to Source Cutoff Voltage	--	--	10		V_{DS} = -15V, I_D = -1µA
$V_{DS(on)}$	Drain to Source On Voltage	--	--	-0.5		V_{GS} = 0V, I_D = -6mA
I_{DSS}	Drain to Source Saturation Current (Note 2)	-10	--	--	mA	V_{DS} = -20V, V_{GS} = 0V
I_{GSS}	Gate Reverse Current	--	--	2	nA	V_{GS} = 15V, V_{DS} = 0V
$I_{D(off)}$	Drain Cutoff Current	--	--	-10		V_{DS} = -15V, V_{GS} = 12V
		--	--	-10	µA	V_{DS} = -15V, V_{GS} = 7V
I_{DGO}	Drain Reverse Current	--	--	-2	nA	V_{DG} = -15V, I_S = 0A
$r_{DS(on)}$	Drain to Source On Resistance	--	--	75	Ω	I_D = -1mA, V_{GS} = 0V

SST5018 DYNAMIC ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
$r_{DS(on)}$	Drain to Source On Resistance	--	--	75	Ω	I_D = 0A, V_{GS} = 0V, f = 1kHz
C_{iss}	Input Capacitance	--	--	45	pF	V_{DS} = -15V, V_{GS} = 0V, f = 1MHz
C_{rss}	Reverse Transfer Capacitance	--	--	10		V_{DS} = 0V, V_{GS} = 12V, f = 1MHz

SST5018 SWITCHING CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC		UNITS	CONDITIONS
$t_{d(on)}$	Turn On Time	15	ns	V_{GS}(L) = 12V V_{GS}(H) = 0V See Switching Circuit
t_r	Turn On Rise Time	20		
$t_{d(off)}$	Turn Off Time	15		
t_f	Turn Off Fall Time	50		

Note 1 - Absolute maximum ratings are limiting values above which SST5018 serviceability may be impaired.
Note 2 – Pulse test: PW≤ 300 µs, Duty Cycle ≤ 3%

SST5018 SWITCHING CIRCUIT PARAMETERS

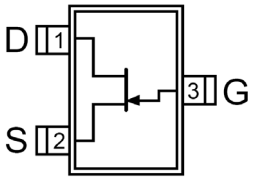
V_{DD}	-6V
V_{GG}	12V
R_L	910Ω
R_G	220Ω
$I_{D(on)}$	-6mA

Available Packages:

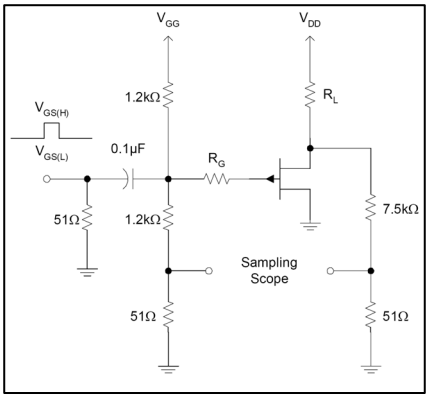
SST5018 in SOT-23
SST5018 in bare die.

Please contact Micross for full package and die dimensions

SOT-23 (Top View)



SWITCHING TEST CIRCUIT



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